

## Standard Rectifier

| 3~<br>Rectifier  |   |        |  |
|------------------|---|--------|--|
| $V_{\text{RRM}}$ | = | 1600 V |  |
| IDAV             | = | 240 A  |  |
| I <sub>FSM</sub> | = | 1300 A |  |

Half 3~ Bridge, Common Anode

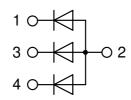
Part number

#### **DMA240YA1600NA**



Backside: isolated





### Features / Advantages:

- Planar passivated chips
- Very low leakage current
- Very low forward voltage drop • Improved thermal behaviour

## **Applications:**

- Diode for main rectification
- For single and three phase bridge configurations

Package: SOT-227B (minibloc)

- Isolation Voltage: 3000 V~ • Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0 • Base plate: Copper
- internally DCB isolated Advanced power cycling

#### Terms and Conditions of Usage

The data contained in this product data sheet is exclusively intended for technically trained staff. The user will have to evaluate the suitability of the product for the intended application and the completeness of the product data with respect to his application. The specifications of our components may not be considered as an assurance of component characteristics. The information in the valid application- and assembly notes must be considered. Should you require product information in excess of the data given in this product data sheet or which concerns the specific application of your product, please contact your local sales office.

Due to technical requirements our product may contain dangerous substances. For information on the types in question please contact your local sales office.

Should you intend to use the product in aviation, in health or life endangering or life support applications, please notify. For any such application we urgently recommend

to perform joint risk and quality assessments;
the conclusion of quality agreements;

- to establish joint measures of an ongoing product survey, and that we may make delivery dependent on the realization of any such measures.

IXYS reserves the right to change limits, conditions and dimensions.

Data according to IEC 60747 and per semiconductor unless otherwise specified

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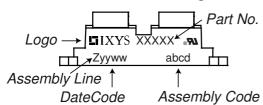
| Rectifier         |                                   |  |                         | 1    | Ratings | S    |      |
|-------------------|-----------------------------------|--|-------------------------|------|---------|------|------|
| Symbol            | Definition                        | Conditions                                 |                         | min. | typ.    | max. | Unit |
| V <sub>RSM</sub>  | max. non-repetitive reverse bloc  | cking voltage                              | $T_{VJ} = 25^{\circ}C$  |      |         | 1700 | V    |
| V <sub>RRM</sub>  | max. repetitive reverse blocking  | voltage                                    | $T_{VJ} = 25^{\circ}C$  |      |         | 1600 | V    |
| I <sub>R</sub>    | reverse current                   | V <sub>R</sub> = 1600 V                    | $T_{VJ} = 25^{\circ}C$  |      |         | 50   | μΑ   |
|                   |                                   | $V_R = 1600 \text{ V}$                     | $T_{VJ} = 150$ °C       |      |         | 1.5  | mΑ   |
| V <sub>F</sub>    | forward voltage drop              | I <sub>F</sub> = 80 A                      | $T_{VJ} = 25^{\circ}C$  |      |         | 1.23 | V    |
|                   |                                   | $I_F = 240 A$                              |                         |      |         | 1.72 | ٧    |
|                   |                                   | I <sub>F</sub> = 80 A                      | T <sub>VJ</sub> = 125°C |      |         | 1.19 | ٧    |
|                   |                                   | $I_F = 240 A$                              |                         |      |         | 1.80 | ٧    |
| I <sub>DAV</sub>  | bridge output current             | T <sub>C</sub> = 100°C                     | T <sub>vJ</sub> = 150°C |      |         | 240  | Α    |
|                   |                                   | rectangular d = ⅓                          |                         |      |         |      |      |
| V <sub>F0</sub>   | threshold voltage                 |  | T <sub>vJ</sub> = 150°C |      |         | 0.86 | V    |
| r <sub>F</sub>    | slope resistance } for power      | loss calculation only                      |                         |      |         | 4    | mΩ   |
| R <sub>thJC</sub> | thermal resistance junction to ca | ase  |                         |      |         | 0.35 | K/W  |
| R <sub>thCH</sub> | thermal resistance case to heats  | sink                                       |                         |      | 0.10    |      | K/W  |
| P <sub>tot</sub>  | total power dissipation           |  | $T_{C} = 25^{\circ}C$   |      |         | 355  | W    |
| I <sub>FSM</sub>  | max. forward surge current        | t = 10 ms; (50 Hz), sine                   | $T_{VJ} = 45^{\circ}C$  |      |         | 1.30 | kA   |
|                   |                                   | t = 8,3 ms; (60 Hz), sine                  | $V_R = 0 V$             |      |         | 1.41 | kA   |
|                   |                                   | t = 10 ms; (50 Hz), sine                   | T <sub>vJ</sub> = 150°C |      |         | 1.11 | kA   |
|                   |                                   | t = 8,3  ms; (60 Hz), sine                 | $V_R = 0 V$             |      |         | 1.20 | kA   |
| l²t               | value for fusing                  | t = 10 ms; (50 Hz), sine                   | $T_{VJ} = 45^{\circ}C$  |      |         | 8.45 | kA2s |
|                   |                                   | t = 8,3 ms; (60 Hz), sine                  | $V_R = 0 V$             |      |         | 8.21 | kA2s |
|                   |                                   | t = 10 ms; (50 Hz), sine                   | $T_{VJ} = 150$ °C       |      |         | 6.11 | kA2s |
|                   |                                   | t = 8.3  ms; (60 Hz), sine                 | $V_R = 0 V$             |      |         | 5.94 | kA2s |
| CJ                | junction capacitance              | $V_{R} = 400 \text{ V}; f = 1 \text{ MHz}$ | $T_{VJ} = 25^{\circ}C$  |      | 48      |      | pF   |



# **DMA240YA1600NA**

| Package                      | SOT-227B (minible  | oc)                                 |                            |     | ı    | Ratings | S    |      |
|------------------------------|--|-------------------------------------|----------------------------|-----|------|---------|------|------|
| Symbol                       | Definition   | Conditions                          |                            |     | min. | typ.    | max. | Unit |
| RMS                          | RMS current  | per terminal                        |                            |     |      |         | 150  | Α    |
| T <sub>VJ</sub>              | virtual junction temperature                                 |                                     |                            |     | -40  |         | 150  | °C   |
| Top                          | operation temperature  |                                     |                            |     | -40  |         | 125  | °C   |
| T <sub>stg</sub>             | storage temperature  |                                     |                            |     | -40  |         | 150  | °C   |
| Weight                       |  |                                     |                            |     |      | 30      |      | g    |
| M <sub>D</sub>               | mounting torque  |                                     |                            |     | 1.1  |         | 1.5  | Nm   |
| $\mathbf{M}_{_{\mathbf{T}}}$ | terminal torque  |                                     |                            |     | 1.1  |         | 1.5  | Nm   |
| d <sub>Spp/App</sub>         | creepage distance on surface   striking distance through air |                                     |                            |     | 3.2  |         |      | mm   |
| d <sub>Spb/Apb</sub>         | creepage distance on suna                                    | ace   striking distance through air | terminal to backside       | 8.6 | 6.8  |         |      | mm   |
| V <sub>ISOL</sub>            | isolation voltage  | t = 1 second                        | 50/60 Hz, RMS; IsoL ≤ 1 mA |     | 3000 |         |      | ٧    |
| 1002                         |  | t = 1 minute                        |                            |     | 2500 |         |      | ٧    |





#### Part description

D = Diode M = Standard Rectifier

A = (up to 1800V)

240 = Current Rating [A]

YA = Half 3~ Bridge, Common Anode

1600 = Reverse Voltage [V]

NA = SOT-227B (minibloc)

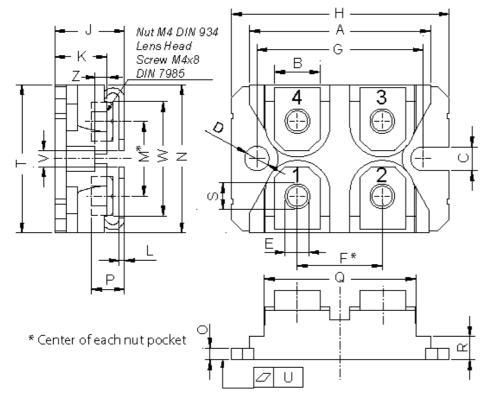
| Ordering | Ordering Number | Marking on Product | Delivery Mode | Quantity | Code No. |
|----------|-----------------|--------------------|---------------|----------|----------|
| Standard | DMA240YA1600NA  | DMA240YA1600NA     | Tube          | 10       | 523282   |

| Similar Part   | Package             | Voltago alago |
|----------------|---------------------|---------------|
| Sillilai Fait  | Fackage             | Voltage class |
| DMA240YC1600NA | SOT-227B (minibloc) | 1600          |

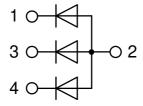
| Equiva              | alent Circuits for | Simulation | * on die level | T <sub>vJ</sub> = 150 °C |
|---------------------|--------------------|------------|----------------|--------------------------|
| $I \rightarrow V_0$ | )— <u>R</u> 0      | Rectifier  |                |                          |
| V <sub>0 max</sub>  | threshold voltage  | 0.86       |                | V                        |
| $R_{0 \text{ max}}$ | slope resistance * | 2.1        |                | $m\Omega$                |



## Outlines SOT-227B (minibloc)



| Dim.   | Millimet |       | r Inches |       |  |
|--------|----------|-------|----------|-------|--|
| DIIII. | min      | max   | min      | max   |  |
| Α      | 31.50    | 31.88 | 1.240    | 1.255 |  |
| В      | 7.80     | 8.20  | 0.307    | 0.323 |  |
| С      | 4.09     | 4.29  | 0.161    | 0.169 |  |
| D      | 4.09     | 4.29  | 0.161    | 0.169 |  |
| Е      | 4.09     | 4.29  | 0.161    | 0.169 |  |
| F      | 14.91    | 15.11 | 0.587    | 0.595 |  |
| G      | 30.12    | 30.30 | 1.186    | 1.193 |  |
| Н      | 37.80    | 38.23 | 1.488    | 1.505 |  |
| J      | 11.68    | 12.22 | 0.460    | 0.481 |  |
| K      | 8.92     | 9.60  | 0.351    | 0.378 |  |
| L      | 0.74     | 0.84  | 0.029    | 0.033 |  |
| M      | 12.50    | 13.10 | 0.492    | 0.516 |  |
| N      | 25.15    | 25.42 | 0.990    | 1.001 |  |
| 0      | 1.95     | 2.13  | 0.077    | 0.084 |  |
| Р      | 4.95     | 6.20  | 0.195    | 0.244 |  |
| Q      | 26.54    | 26.90 | 1.045    | 1.059 |  |
| R      | 3.94     | 4.42  | 0.155    | 0.167 |  |
| S      | 4.55     | 4.85  | 0.179    | 0.191 |  |
| Т      | 24.59    | 25.25 | 0.968    | 0.994 |  |
| U      | -0.05    | 0.10  | -0.002   | 0.004 |  |
| V      | 3.20     | 5.50  | 0.126    | 0.217 |  |
| W      | 19.81    | 21.08 | 0.780    | 0.830 |  |
| Ζ      | 2.50     | 2.70  | 0.098    | 0.106 |  |





## Rectifier

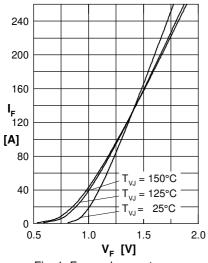


Fig. 1 Forward current versus voltage drop per diode

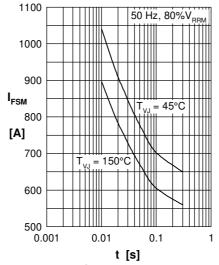


Fig. 2 Surge overload current vs. time per diode

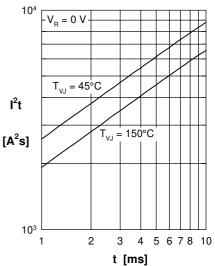


Fig. 3 I<sup>2</sup>t versus time per diode

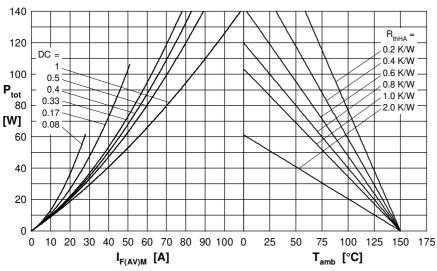


Fig. 4 Power dissipation vs. forward current and ambient temperature per diode

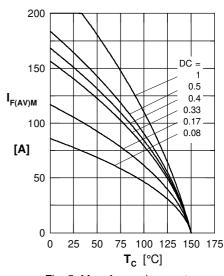


Fig. 5 Max. forward current vs. case temperature per diode

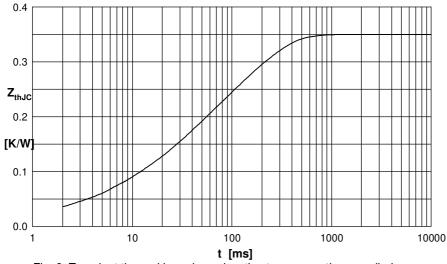


Fig. 6 Transient thermal impedance junction to case vs. time per diode

Constants for  $Z_{thJC}$  calculation:

| i | $R_{thi}$ (K/W) | t <sub>i</sub> (s) |
|---|-----------------|--------------------|
| 1 | 0.0200          | 0.01000            |
| 2 | 0.0120          | 0.00001            |
| 3 | 0.0280          | 0.00400            |
| 4 | 0.1000          | 0.03000            |
| 5 | 0.1900          | 0.16000            |